

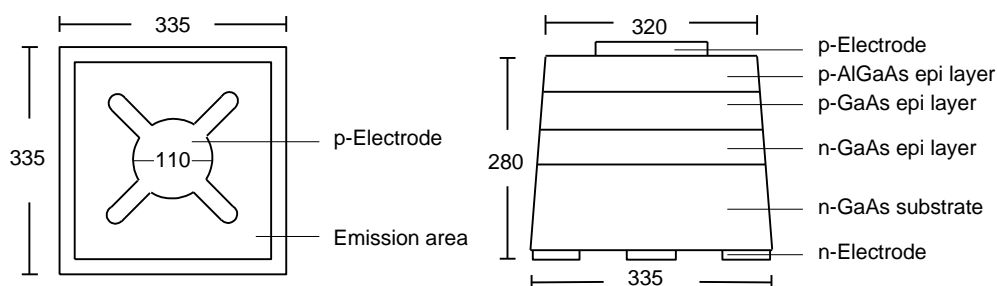
■ Features :

- AlGaAs/GaAs Wafer
- Good Spectral Matched to Si Detector
- High Power
- Low Forward Voltage

■ Typical Applications :

- Remote Controller
- Peripherals
- Photo Coupler
- Photo Interrupter

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

| | | |
|-------------------|-----------------------------------|---------------------------------------|
| Chip dimension | Chip size | 335 μm x 335 μm |
| | Thickness | 280 μm |
| | Emission area | 320 μm |
| | Bonding pad | 110 μm |
| Electrode | Top: P (anode) | Gold (Aluminum optional) |
| | Backside: N (cathode) | Gold alloy |
| Surface condition | Frosted (Smooth for Aluminum pad) | |

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|-------------------------------|-----------------|------------------------|------|------|------|------|
| Forward Voltage | V_F | $I_F = 100 \text{ mA}$ | - | 1.32 | 1.50 | V |
| | | $I_F = 200 \text{ mA}$ | - | 1.58 | 1.65 | |
| Reverse Voltage | V_R | $I_R = 10 \text{ uA}$ | 5 | - | - | V |
| Wavelength | λ_p | $I_F = 20 \text{ mA}$ | - | 940 | - | nm |
| Spectral width at half height | $\Delta\lambda$ | $I_F = 20 \text{ mA}$ | - | 50 | - | nm |
| Radiant Power | P_o | $I_F = 20 \text{ mA}$ | 0.50 | 0.91 | - | mW |

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. DC Forward Voltage

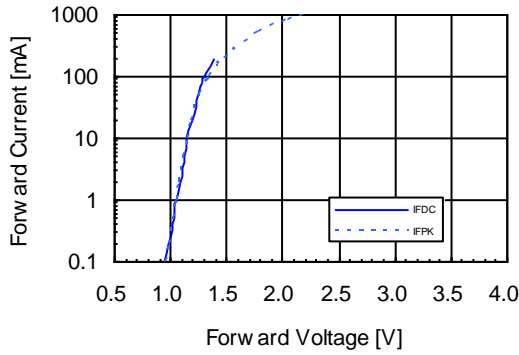


Fig 2. Relative Radian Power vs. Wavelength

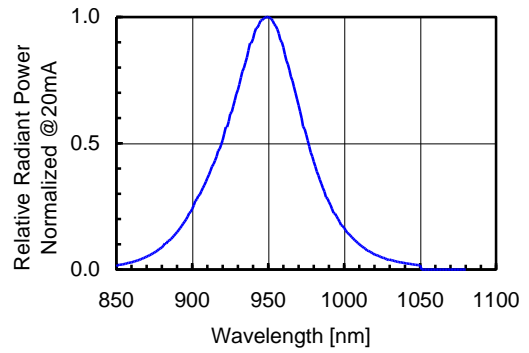


Fig 3. Relative Radiant Power vs. Forward DC Current

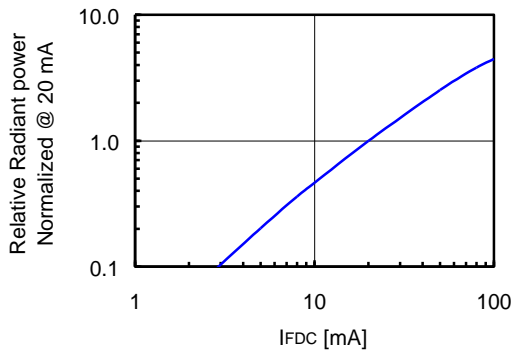


Fig 4. Relative Radiant Power Vs. Forward Peak Current

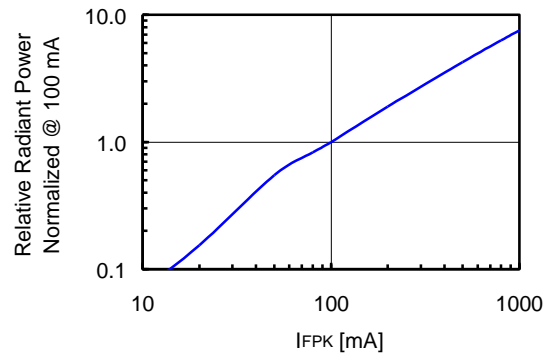


Fig 5. Forward DC Voltage vs. Temperature

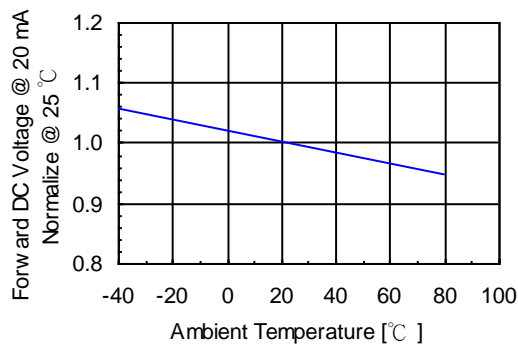


Fig 6. Relative Radiant Power vs. Temperature

